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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of

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Application Number	10/581,797 - Conf. # 4944		
Filing Date	June 2, 2006		
First Named Inventor	Yang Yang		
Art Unit	2818		
Examiner Name	Long K. Tran		
Attorney Docket Number	58086-231274		

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Examiner Initials*	Cite No.1	Document Number  Number-Kind Code <sup>2</sup> ( if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Initials*	No.1	Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)	Date MM-DD-YYYY	Applicant of Cited Document	Or Relevant Figures Appear	
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Examiner Name	Long K. Tran
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Sheet	6	of	6	Attorney Docket Number	58086-231274

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